

TOSHIBA GATE TURN-OFF THYRISTOR

SG2000R24, SG2000U24, SG2000W24, SG2000EX24

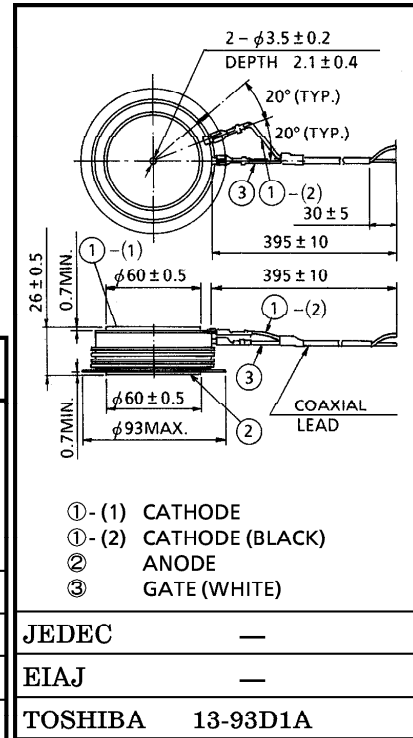
CHOPPER, INVERTER APPLICATION

Unit in mm

- Repetitive Peak Off-State Voltage : $V_{DRM}=1300, 1600, 1800, 2500V$
- R.M.S On-State Current : $I_T (RMS)=1050A$
- Peak Turn-Off Current : $I_{TGQM}=2000A$
- Critical Rate of Rise of On-State Current : $di/dt=300A/\mu s$
- Critical Rate of Rise of Off-State Voltage : $dv/dt=1000V/\mu s$

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Off-State Voltage (Note 1)	SG2000R24	1300	V
	SG2000U24	1600	
	SG2000W24	1800	
	SG2000EX24	2500	
Repetitive Peak Reverse Voltage	V_{RRM}	16	V
Peak Turn-Off Current (Note 2)	I_{TGQM}	2000	A
R.M.S On-State Current (Note 3)	$I_T (RMS)$	1050	A
Peak One Cycle Surge On-State Current (Non-Repetitive, 10ms Width Half Sine Waveform)	I_{TSM}	14000	A
Critical Rate of Rise of On-State Current (Note 4)	di/dt	300	$A/\mu s$
Peak Forward Gate Current	I_{FGM}	70	A
Average Forward Gate Power Dissipation	$P_{FG (AV)}$	14	W
Average Reverse Gate Power Dissipation	$P_{RG (AV)}$	120	W
R.M.S Gate Current (Note 5)	$I_G (RMS)$	42	A
Peak Reverse Gate Voltage (at Static)	V_{RGM}	16	V
Operating Junction Temperature Range	T_j	-40~125	°C
Storage Temperature Range	T_{stg}	-40~150	°C
Mounting Force	—	19.6 ± 2.0	kN



JEDEC	—
EIAJ	—
TOSHIBA	13-93D1A

Weight : 800g

- Note 1. $R_{GK}=10\Omega$
- Note 2. $C_S=4\mu F, R_S=5\Omega, di_{GQ}/dt=40A/\mu s, I_{GQ}=450A, V_{DM}=V_{DRM}, T_j=125^\circ C$
 $V_{DSP} \leq 600V, L_S \leq 0.3\mu H$
- Note 3. Half Sine Waveform $T_f=80^\circ C$
- Note 4. $V_D=1/2$ Rated, $I_G=30A$
- Note 5. Ambient Temperature of coaxial gate-cathode lead = $90^\circ C$

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ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Repetitive Peak Off-State Current	I_{DRM}	$V_{DRM} = \text{Rated}$, $R_{GK} = 10\Omega$, $T_j = 125^\circ\text{C}$	—	—	50	mA	
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM} = \text{Rated}$, $T_j = 125^\circ\text{C}$	—	—	10	mA	
Repetitive Peak Reverse Gate Current	I_{RGM}	$V_{RGM} = \text{Rated}$, $T_j = 125^\circ\text{C}$	—	—	10	mA	
Peak On-State Voltage	V_{TM}	$I_{TM} = 2000\text{A}$, $T_j = 125^\circ\text{C}$	—	—	2.4	V	
Gate Trigger Voltage	V_{GT}	$V_D = 24\text{V}$, $R_L = 0.1\Omega$	$T_j = -40^\circ\text{C}$	—	—	1.5	V
	$T_j = 25^\circ\text{C}$		—	—	1.0		
Gate Trigger Current	I_{GT}		$T_j = -40^\circ\text{C}$	—	—	6.0	A
			$T_j = 25^\circ\text{C}$	—	—	2.5	
Turn-On Delay Time	t_d	$V_D = 1/2 \text{ Rated}$, $di/dt = 300\text{A}/\mu\text{s}$, $I_{TM} = 2000\text{A}$, $I_G = 30\text{A}$, $t_r = 1\mu\text{s}$, $T_j = 25^\circ\text{C}$	—	—	2.0	μs	
Turn-On Time	t_{gt}		—	—	10	μs	
Critical Rate of Rise of Off-State Voltage	dv/dt	$V_{DRM} = 2/3 \text{ Rated}$, $T_j = 125^\circ\text{C}$, $V_{GK} = -2\text{V}$, Exponential Rise	1000	—	—	$\text{V}/\mu\text{s}$	
Storage Time	t_s	$I_T = 2000\text{A}$, $V_D = 1/2 \text{ Rated}$, $V_{DM} = V_{DRM}$, $C_S = 4\mu\text{F}$, $di_{GQ}/dt = 40\text{A}/\mu\text{s}$, $T_j = 125^\circ\text{C}$, $L_S \leq 0.3\mu\text{H}$	—	—	20	μs	
Gate Turn-Off Time	t_{gq}		—	—	23	μs	
Tail Time	t_{tail}		—	—	60	μs	
Gate Turn-Off Current	I_{GQ}		—	450	—	A	
Thermal Resistance (Junction to Fin)	$R_{th(j-f)}$	DC	—	—	0.02	$^\circ\text{C}/\text{W}$	

